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SEMICONDUCTOR

March 2007

FODM3062/FODM3063/FODM3082/FODM3083 4-Pin Full Pitch Mini-Flat Package Zero-Cross Triac **Driver Output Optocouplers**

Features

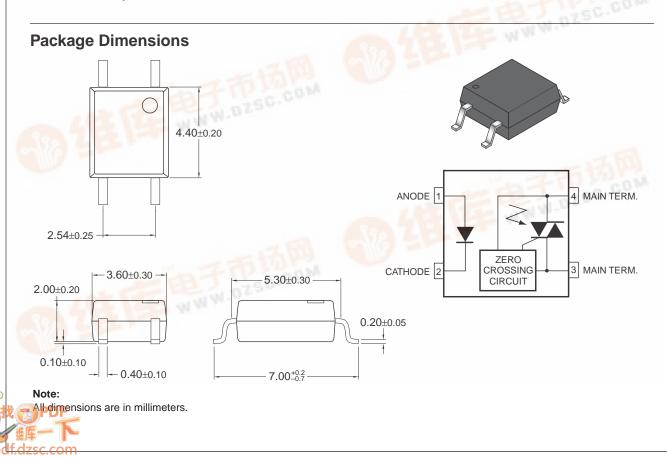
- dv/dt of 600V/µs guaranteed
- Compact 4-pin surface mount package (2.4mm maximum standoff height)
- Zero voltage crossing
- Peak blocking voltage: 600V (FODM306X) 800V (FODM308X)
- Available in tape and reel quantities of 500 and 2500.
- C-UL, UL and VDE certifications pending

Applications

- Solenoid/valve controls
- Lighting controls
- Static power switches
- AC motor drives
- Temperature controls
- E.M. contactors
- AC motor starters
- Solid state relays

Description

The FODM306X and FODM308X series consist of an infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver, and is housed in a compact 4-pin mini-flat package. The lead pitch is 2.54mm. They are designed for use with a triac in the interface of logic systems to equipment powered from 115/240 VAC lines, such as solid state relays, industrial controls, motors, solenoids and consumer appliances.



Symbol	Parame	Rating	Units	
TOTAL PACKA	GE			
T _{STG}	Storage Temperature	-55 to +150	°C	
T _{OPR}	Operating Temperature		-40 to +100	°C
EMITTER			44	
I _{F (avg)}	Continuous Forward Current	60	mA	
I _{F (pk)}	Peak Forward Current (1µs pulse, 300pps.)		1	А
V _R	Reverse Input Voltage		6	V
PD	Power Dissipation (No derating required over operating temp. range)		100	mW
DETECTOR				
I _{T(RMS)}	On-State RMS Current		70	mA (RMS)
V _{DRM}	Off-State Output Terminal Voltage FODM3062/FODM3063		600	V
		FODM3082/FODM3083	800	
P _D	Power Dissipation (No derating require	ed over operating temp. range)	300	mW

Electrical Characteristics (T_A = 25°C)

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.*	Max.	Units
EMITTER	I			!	1	!
V _F	Input Forward Voltage	I _F = 30mA			1.5	V
I _R	Reverse Leakage Current	$V_R = 6V$			100	μA
DETECTO	R			!	1	!
I _{DRM1}	Peak Blocking Current, Either Direction	Rated V _{DRM} , $I_F = 0^{(1)}$			500	nA
dV/dt	Critical Rate of Rise of Off-State Voltage	$I_{\rm F} = 0 \; ({\rm Figure \; 1})^{(2)}$	600			V/µs

Transfer Characteristics

Symbol	DC Characteristics	Test Conditions	Device	Min.	Тур.*	Max.	Units
I _{FT}	LED Trigger Current	Main Terminal	FODM3062			10	mA
		Voltage = $3V^{(3)}$	FODM3082				
			FODM3063			5	
			FODM3083				
Ι _Η	Holding Current, Either Direction		All		300		μA
V_{TM}	Peak On-State Voltage, Either Direction	I _F = Rated I _{FT} , I _{TM} = 100mA peak	All			3	V

Zero Crossing Characteristics

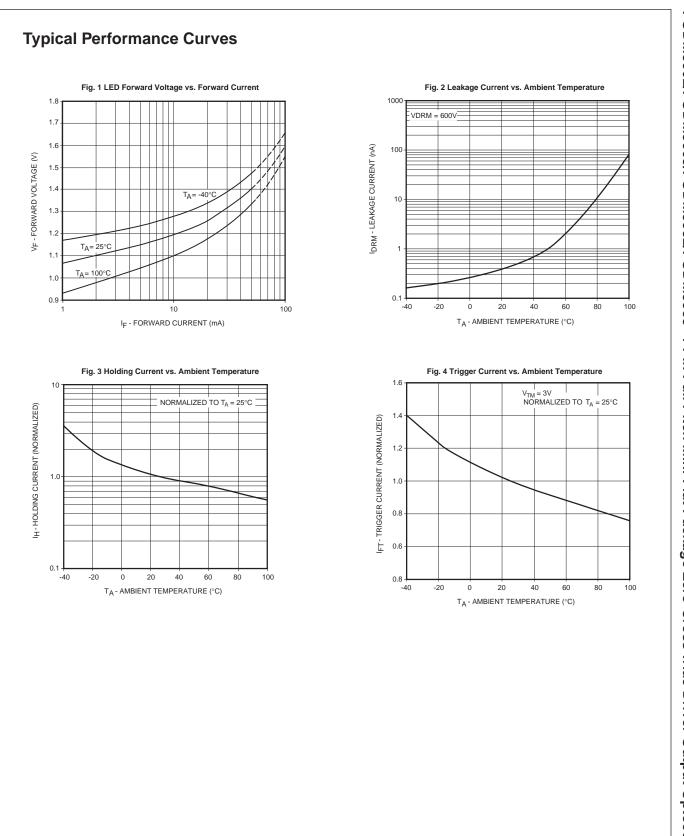
Symbol	Characteristics	Test Conditions	Device	Min.	Тур.*	Max.	Units
V _{IH}	Inhibit Voltage, MT1-MT2 Voltage above which device will not trigger	I _F = Rated I _{FT}	All			20	V
IDRM2	Leakage in Inhibit State	I _F = Rated I _{FT} , Rated VDRM, Off-State	All			500	μΑ

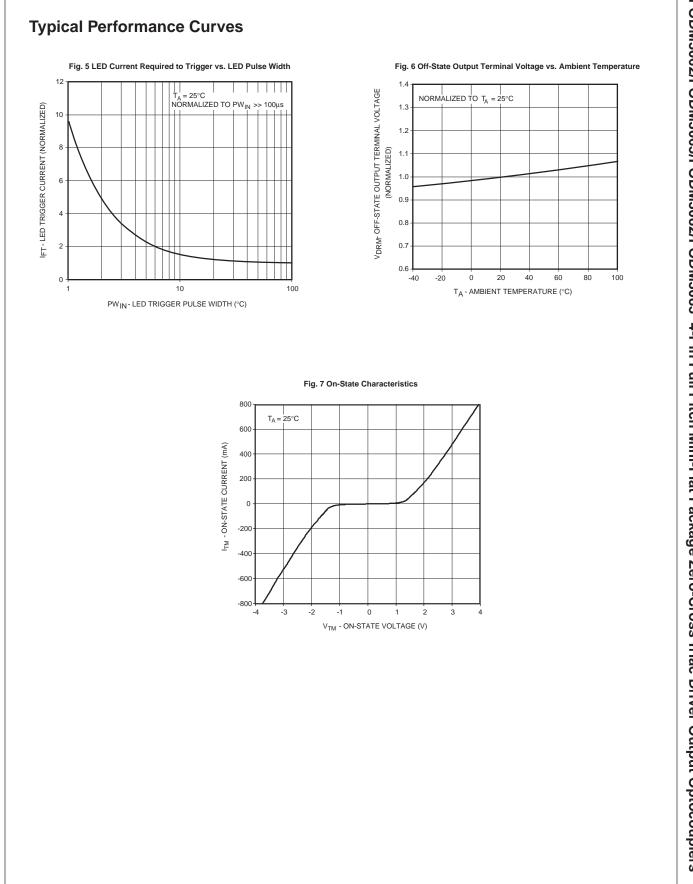
Isolation Characteristics

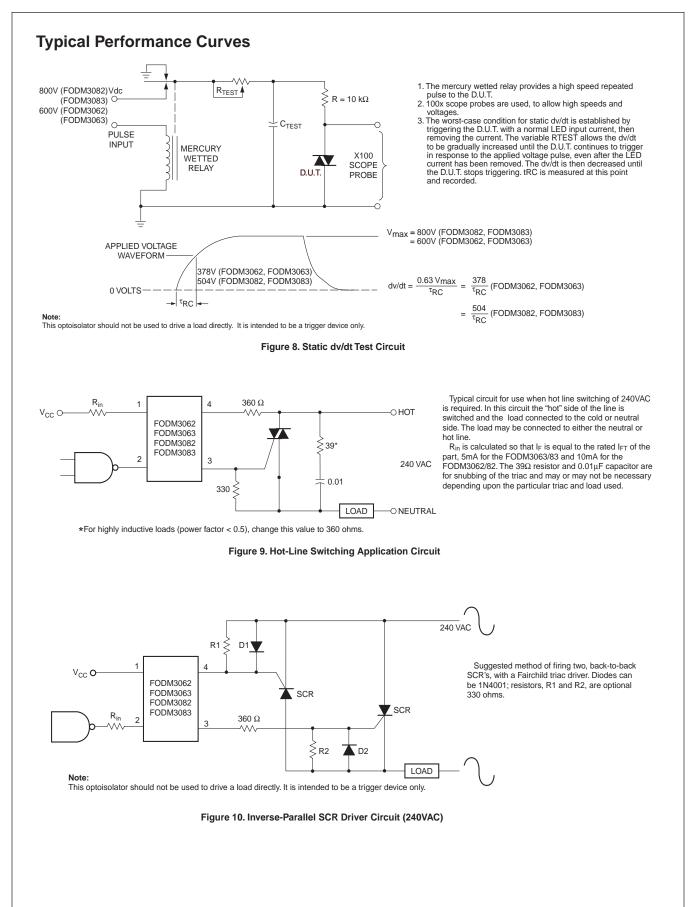
Characteristics	Test Conditions	Symbol	Device	Min.	Тур.*	Max.	Units
Steady State Isolation Voltage ⁽⁴⁾	(1 Minute) R.H. = 40% to 60%	V _{ISO}	All	3750			VRMS

Notes:

- * All typicals at 25°C.
- 1. Test voltage must be applied within dv/dt rating.
- 2. This is static dv/dt. See Figure 1 for test circuit. Commutating dv/dt is function of the load-driving thyristor(s) only.
- 3. All devices are guaranteed to trigger at an I_F value less than or equal to max I_{FT}. Therefore, recommended operating I_F lies between max I_{FT} (10mA for FODM3062/82, 5mA for FODM3063/83) and absolute max I_F (60 mA).
- 4. Steady state isolation voltage, V_{ISO}, is an internal device dielectric breakdown rating. For this test, pins 1 & 2 are common, and pins 3 & 4 are common.

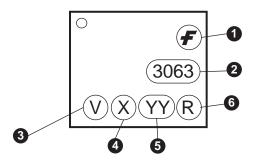




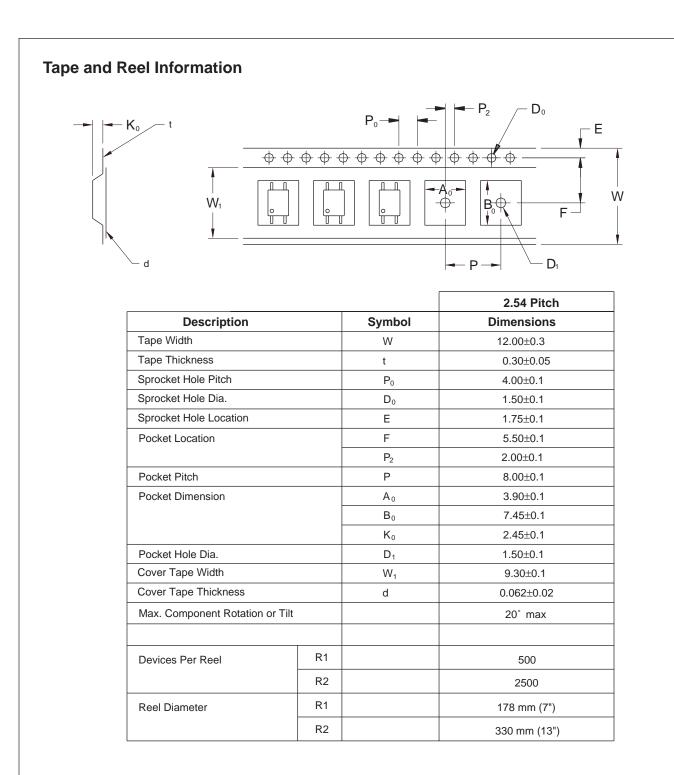


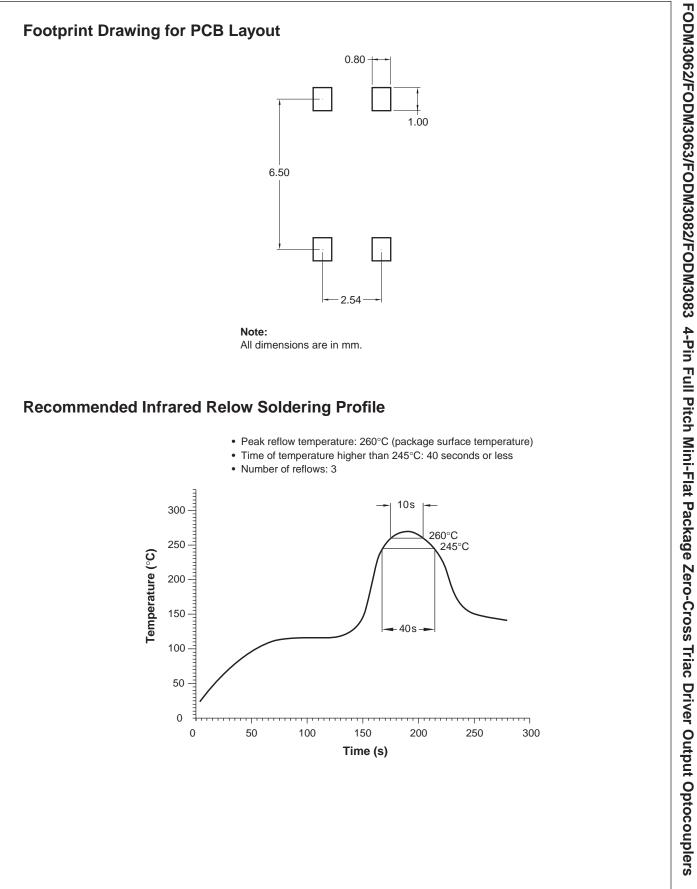
Option	Description
No option	Bulk (100 units/tube)
V	VDE Approved
R1	Tape and Reel (500 units)
R2	Tape and Reel (2500 units)
R1V	Tape and Reel (500 units) and VDE Approved
R2V	Tape and Reel (2500 units) and VDE Approved

Marking Information



Definiti	ons
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code
5	Two digit work week ranging from '01' to '53'
6	Assembly package code





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